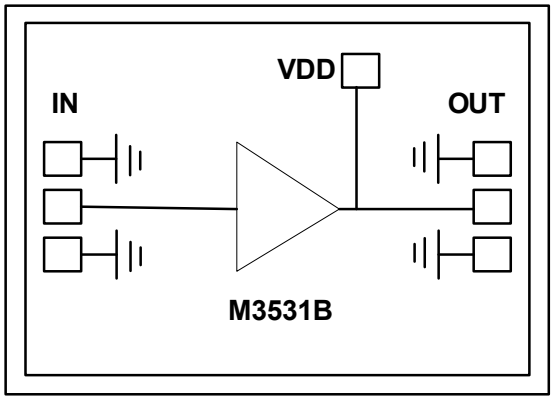
1. Description

- The M3531B is a LNA fabricated on GaAs p-HEMT MMIC process. It operates over 22-33GHz and provides 18dB gain with 1.7dB noise figure and OP_{-1dB} of 10dBm. It can be biased from a single positive supply of 5V.



M3531B-PDS-F01

Figure 1. M3531B Functional Block Diagram

2. Applications

- Microwave Transceiver Modules

3. Features[1]

- Frequency Range: 22-33GHz
- Typical Gain: 18dB, 3dB positive slope
- Noise Figure: 1.7dB
- Input/Output Return Loss: -15dB
- Output P_{-1dB}: 10dBm
- Single Positive Supply: +5V (I_{DQ}=63mA)
- Die Size: 1.6 x 0.85 x 0.10mm

[1] On-wafer Test

4. Brief Typical Performance

Table 1. Brief Typical Performance

Parameter	22-33GHz	Units
Small-Signal Gain	18	dB
Noise Figure	1.7	dB
Input Return Loss	-15	dB
Output Return Loss	-15	dB
Output P_{-1dB}	10	dBm

Table of Contents

No.	Contents	Page
1	Description	1
2	Applications	1
3	Features	1
4	Brief Typical Performance	1
5	Absolute Maximum Ratings	3
6	Recommended Operating Conditions	3
7	RF Characteristics	3
8	Typical Performance Curve	4
9	Outline Dimensions	5
10	Assembly Information	6
11	Handling Precautions	6
12	Contact Information	7
13	Disclaimer	7

5. Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Operating Voltage Range	V_D	0 ~ +6	V
Maximum Input Power	P_{IN}	16	dBm
Storage Temperature Range	T_{STG}	- 55 ~ 150	°C

6. Recommended Operating Conditions

Table 3. Recommended Operating Conditions

Parameter	Min.	Typ.	Max.	Units
Operating Temperature Range	-55	25	125	°C
Supply Voltage, V_D	-	5	-	V
Quiescent Current, I_{DQ}	-	63	-	mA

7. RF Characteristics (V_D=5V, T_C = 25˚C)

Table 4. RF Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Units
Small-Signal Gain	Gain	-	18	-	dB
Noise Figure	NF	-	1.7	-	dB
Input Return Loss	RL_{IN}	-	-15	-	dB
Output Return Loss	RL_{OUT}	-	-15	-	dB
Output Power for 1dB Compression	OP_{-1dB}	-	10	-	dBm

8. Typical Performance Curve (T_C = 25˚C)

■ Small-signal Characteristics Curve

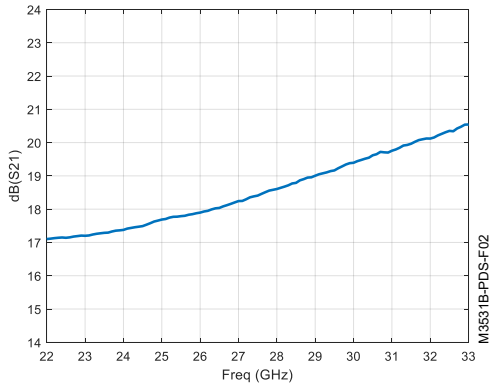


Figure 2. Small-signal Gain Characteristics

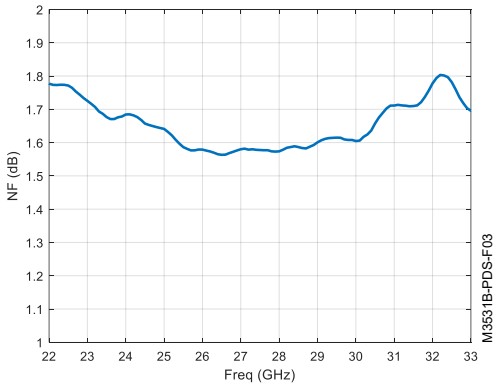


Figure 3. Noise Figure Characteristics

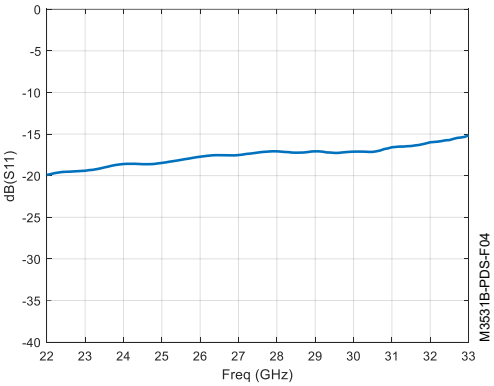


Figure 4. Input Return Loss Characteristics

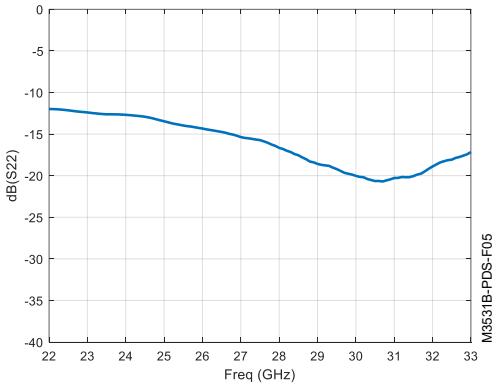


Figure 5. Output Return Loss Characteristics

■ Power Characteristic Curve（V_{DD}=5V, On-wafer test）

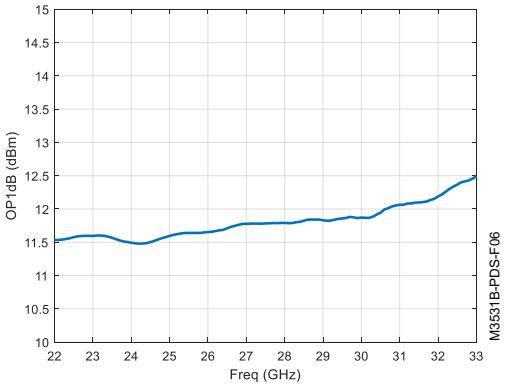
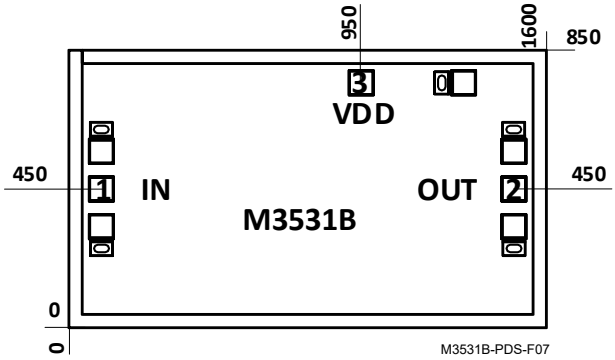


Figure 6. OP_{-1dB} Characteristics

9. Outline Dimensions



• Dimensions shown in micrometre

Figure 7. M3531B Outline Dimensions

Table 4. Pad Description

Pad	Symbol	Description
1	IN	RF Input. 50ohm. DC blocking capacitor is not required.
2	OUT	RF Output. 50ohm. DC blocking capacitor is not required.
3	VDD	Supply Voltage. External bypass capacitors are required, refer to Figure 8.

10. Assembly Information

■ Assembly Diagram

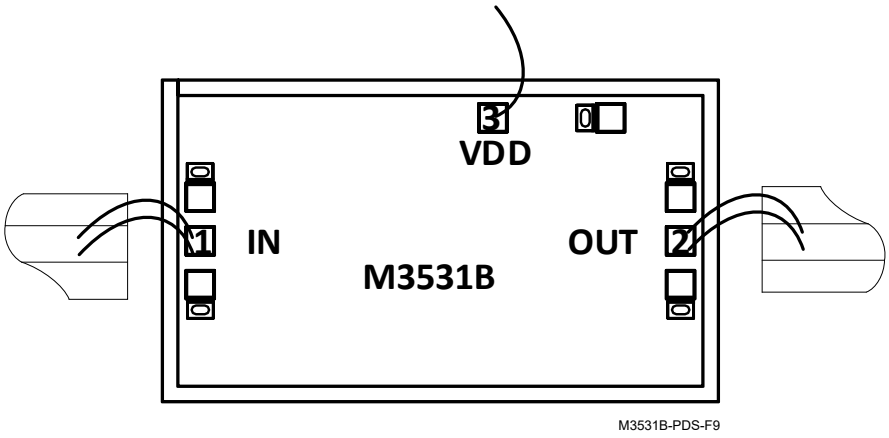


Figure 8. M3531B Assembly Diagram

- **Eutectic Die Attach:** It is best to use an 80% Au/20% Sn preform. Do not expose the chip to a temperature greater than 300°C for more than 30sec.
- **Wire Bonding:** RF bonds made with 1mil gold wire are recommended for the RF ports. Keep all bonds as short as possible, less than 0.35mm.

11. Handling Precautions

- **Storage**
  All bare dies ship in either Waffle or Gel Pak, which is an ESD protective container, and then sealed in an ESD protective bag. After opening the sealed ESD protective bag, all dies must be stored in a dry nitrogen environment.
- **Cleanliness**
  Handle the dies in a clean environment. Never use liquid cleaning systems to clean the dies.
- **ESD Caution**
  ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore proper ESD precautions should be taken to avoid performance degradation or loss of functionality.



12. Contact Information

For the latest specifications, additional product information, technical support and sales support, please contact:

- **Email:** RF.support@raytrontek.com
- **Web:** www.raytrontek.com

13. Disclaimer

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